

Silicon Epitaxial Planar Transistor

2SA1036

FEATURES

- Large $I_{C,ICMAX.} = -500\text{mA}$.
- Low $V_{CE(sat)}$. Ideal for low-voltage operation.
- Complements the 2SC2411.



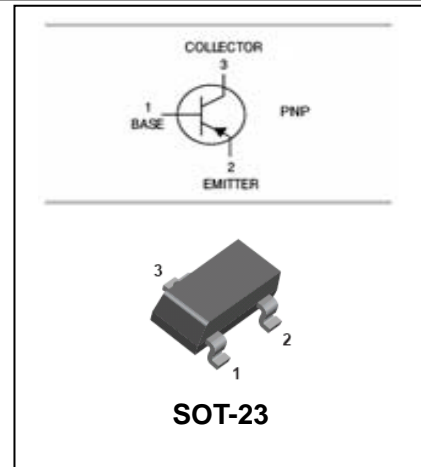
Lead-free

APPLICATIONS

- Ideal for low-voltage operation.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1036	HP/HQ/HR	SOT-23



MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-32	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-500	mA
P_C	Collector Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$

Silicon Epitaxial Planar Transistor

2SA1036

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-20V, I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-1	μA
DC current gain	h_{FE}	$V_{CE}=-3V, I_C=-10mA$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$			-0.4	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-20mA$ $f=100MHz$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		7		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	P	Q	R
Range	82-180	120-270	180-390

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

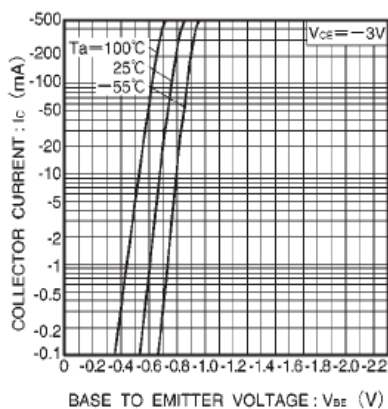


Fig.1 Grounded emitter propagation

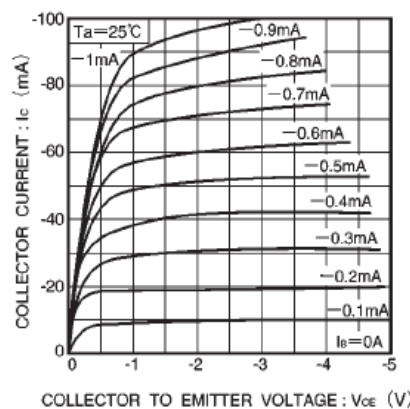


Fig.2 Grounded emitter output characteristics (I)

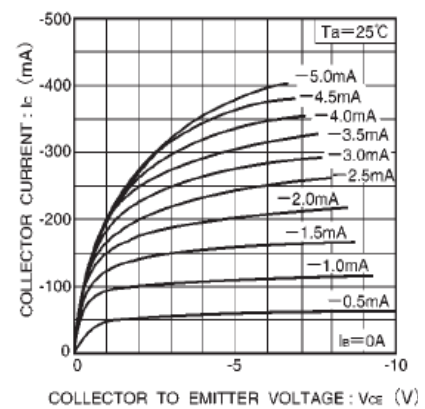


Fig.3 Grounded emitter output characteristics (II)

Silicon Epitaxial Planar Transistor

2SA1036

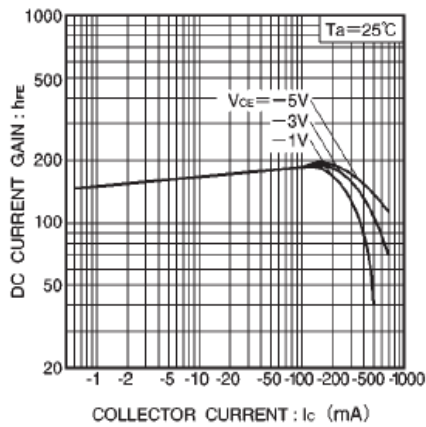


Fig.4 DC current gain vs. collector current (I)

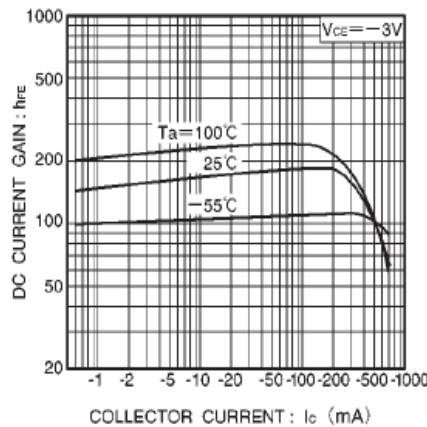


Fig.5 DC current gain vs. collector current (II)

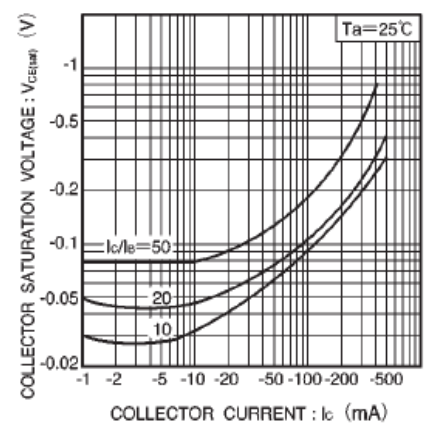


Fig.6 Collector-emitter saturation voltage vs. collector current (I)

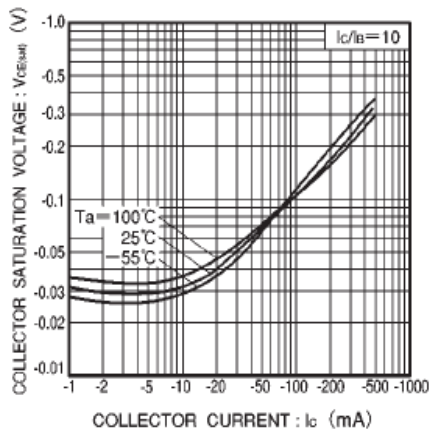


Fig.7 Collector-emitter saturation voltage vs. collector current (II)

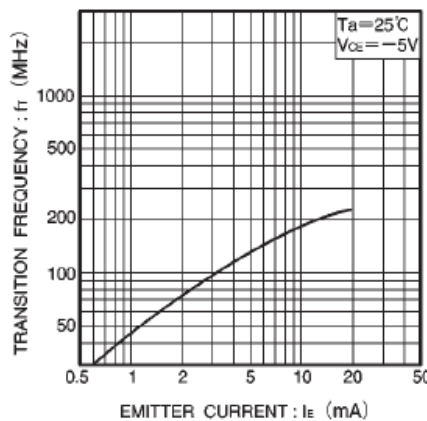


Fig.8 Gain bandwidth product vs. emitter current

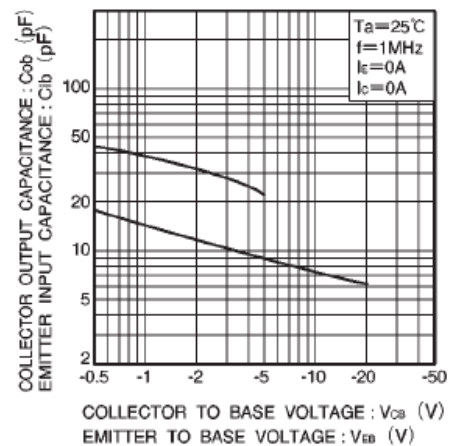


Fig.9 Collector output capacitance vs. collector-base voltage. Emitter input capacitance vs. emitter-base voltage

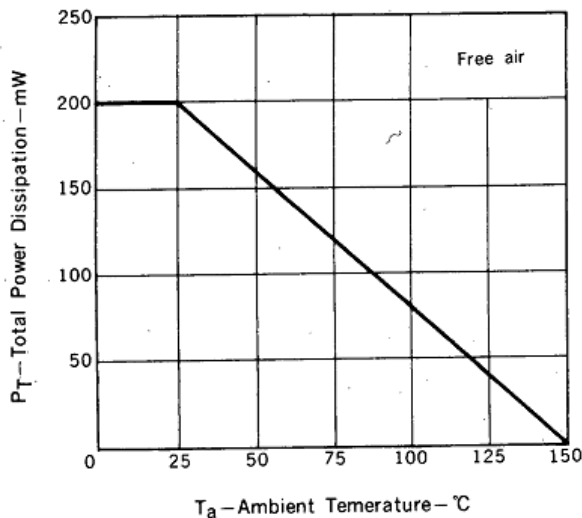


Fig.10 TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE

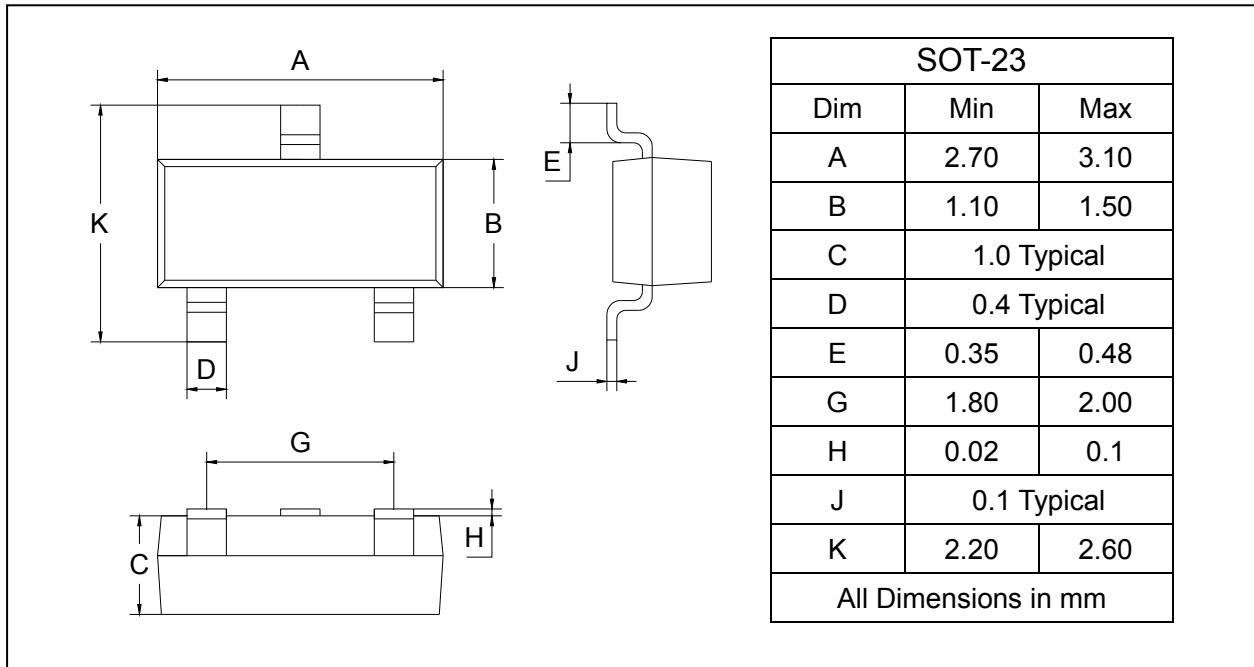
Silicon Epitaxial Planar Transistor

2SA1036

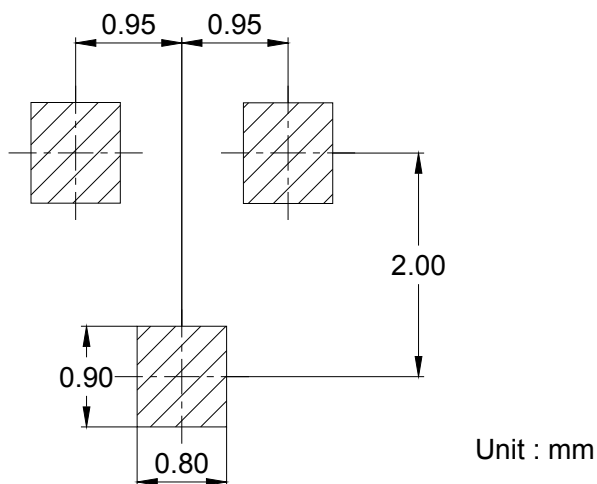
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SA1036	SOT-23	3000/Tape&Reel